RESPONSE TO RESTRICTION REQUIREMENT AND SUPPLEMENTAL AMENDMENT

Serial Number: 10/003240

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Title: ETCHANT FORMULATION FOR SELECTIVELY REMOVING THIN FILMS IN THE PRESENCE OF COPPER, TIN, AND LEAD

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(INTEL)

Assignee: Intel Corporation

IN THE SPECIFICATION

Please amend the specification as follows.

Please amend the paragraph beginning at page 7, line 26 as follows:

Another metal stack embodiment includes metal first layer 26 of Ti at about 1,000 Å, metal second layer 28 selected from doped Ti, Ti, and TiW at about 1,000 Å, metal third layer 30 of Ti at about 1,000 Å, and metal upper layer 32 of nitrided NiV at about 4,000 Å. Another metal stack embodiment includes metal first layer 26 of Ti at about 500 Å, metal second layer 28 selected from doped Ti, doped Ti, and TiW at about 1,000 Å, metal third layer 30 of Ti at about 500 Å, and metal upper layer 32 of nitrided NiV at about 2,000 Å.

Please amend the paragraph beginning at page 11, line 7 as follows:

The ammonium hydroxide compound is selected from is selected from methyl ammonium hydroxide, tetra methyl ammonium hydroxide (TMAH), and the like. In one embodiment, the ammonium hydroxide compound is 25% TMAH in water that is provided in a ratio of about 2 volume parts to about 5 volume parts nitrogen-containing heterocyclic compound, to about 2 volume parts oxidizer.